加急出货

2SD1707

Silicon NPN Epitaxial Planar Type

Power Switching Complementary Pair with 2SB1156

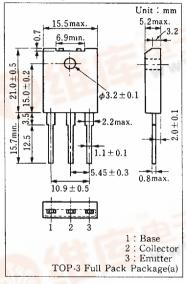
■ Features

- Low collector-emitter saturation voltage (V_{CE(sat)})
- Good linearity of DC current gain (hFE)
- High collector current (I_C)
- "Full Pack" package for simplified mounting on a heat sink with one

■ Absolute Maximum Ratings (Tc=25°C)

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Item Collector-base voltage		Symbol	Value	Unit	
		V_{CBO}	130	V	
Collector-emitter voltage		VCFO	80	V	
Emitter-base voltage		V_{EBO}	7	V	
Peak collector current		I _{CP}	30	А	
Collector current		Ic	20	A	
Collector power dissipation	Tc=25 °C	P_C	100	W	
	Ta=25 °C	PC	3	VV	
Junction temperature		Т,	150	c	
Storage temperature		Tstg	$-55 \sim +150$	°	

■ Package Dimensions

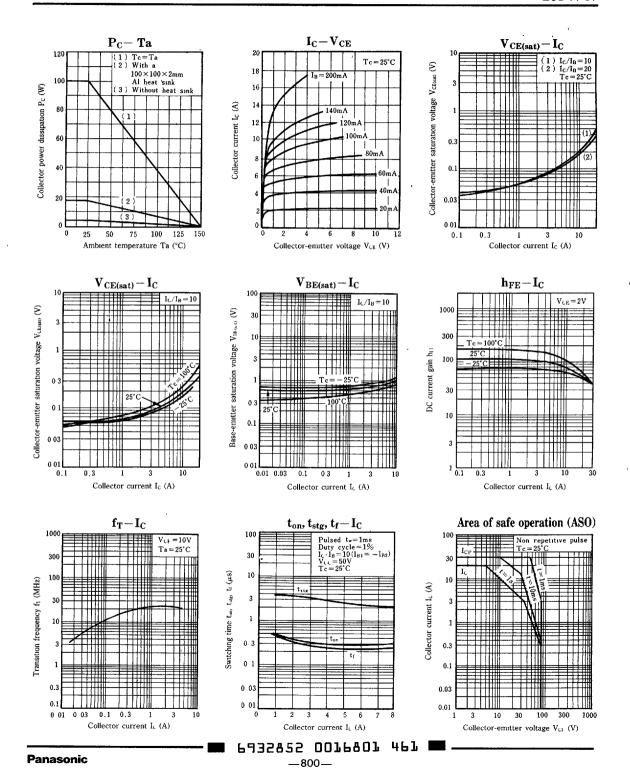


Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 100 \text{ V}, I_E = 0$!	10	μА
Emitter cutoff current	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$			50	μA
Collector-emitter voltage	VCEO	$I_C = 10 \text{ mA}, I_B = 0$	80		1	V
	h _{FE1}	$V_{CF} = 2 \text{ V}, I_{C} = 0.1 \text{ A}$	45			
DC current gain	hFE2*	$V_{CE} = 2 V$, $I_C = 3 A$	60		260	W
!	h _{FE3}	$V_{CE} = 2 \text{ V}, I_{C} = 10 \text{ A}$	30			V
Collector-emitter saturation voltage	V _{CE(sat)1}	$I_C = 8 \text{ A}, I_B = 0.4 \text{ A}$	N/P		0.5	V
Collector-enlitter saturation voltage	VCE(sat)2	$I_{c} = 20 \text{ A}, I_{B} = 2 \text{ A}$			1.5	V
Base-emitter saturation voltage	VBE(sat)1	$I_{\rm C} = 8 {\rm A}, \ I_{\rm B} = 0.4 {\rm A}$			1.5	V
Dase-enlitter saturation voltage	VBE(sat)2	$I_{c} = 20 \text{ A}, I_{B} = 2 \text{ A}$			2.5	
Transition frequency	fr	$V_{CE} = 10V, I_{C} = 0.5A, f = 1MHz$		20		MHz
Turn-on t <mark>ime</mark>	ton	T 01 T 001 T 001		0.5		μS
Storage time	tstg	$I_C=8A$, $I_{B1}=0.8A$, $I_{B2}=-0.8A$ $V_{CC}=50V$		2.0		μS
Fall time	tí	V CC - 30 V		0.2		μS

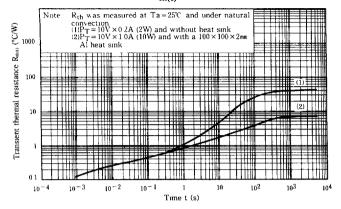
hFE2 Classifications

Class	R	Q	P
D F.2	60~120	90~180	130~260

6932852 0016800 525



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